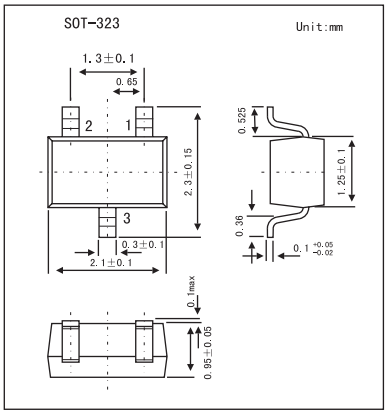
Silicon Schottky Barrier Diode

HSB88WA



■ Features

- Low reverse current, Low capacitance.
- CMPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	10	V
Average rectified current	I_O	15	mA
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	I_F =1 mA	0.35		0.42	V
		I_F =10 mA	0.50		0.58	
Reverse current	I_R	V_R =2 V			0.2	μA
		V_R =10 V			10	
Capacitance	C	V_R = 0 V, f = 1 MHz			0.80	pF
Capacitance deviation	ΔC	V_R = 0V, f = 1 MHz			0.10	pF
Forward voltage deviation	ΔV_F	I_F = 10 mA			10	mV
ESD-Capability (Note 1)		C=200 pF, R= 0Ω Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ; $I_R \geqslant$ 0.4 μA at V_R =2 V

■ Marking

Marking	C7